

2^{nd} Generation thinQ!TM SiC Schottky Diode

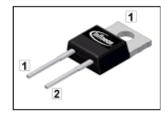
Features

- Revolutionary semiconductor material Silicon Carbide
- Switching behavior benchmark
- No reverse recovery/ No forward recovery
- No temperature influence on the switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target applications
- Breakdown voltage tested at 5mA²⁾

Product Summary

V _{DC}	600	V
Q_{c}	8	nC
I _F	4	Α

PG-T0220-2



thinQ! 2G Diode specially designed for fast switching applications like:

- CCM PFC
- Motor Drives

Туре	Package	Marking	Pin 1	Pin 2
IDH04S60C	PG-TO220-2	D04S60C	С	А

Maximum ratings, at T_j =25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous forward current	I _F	T _C <140 °C	4	А
RMS forward current	I _{F,RMS}	f=50 Hz	5.6	
reasonably be expected to cause the failure of that life-support , automotive, aviation and	I _{F,SM}	$T_{\rm C}$ =25 °C, $t_{\rm p}$ =10 ms	32	
Life support systems are intended to b	I _{F,RM}	T _j =150 °C, T _C =100 °C, D=0.1	18	
and sustain and/or protect human life.	I _{F,max}	$T_{\rm C}$ =25 °C, $t_{\rm p}$ =10 μs	132	
of the user or other persons may be e	V_{RRM}		600	V
Diode dv/dt ruggedness	d <i>v</i> /d <i>t</i>	V _R = 0480V	50	V/ns
Power dissipation	P_{tot}	T _C =25 °C	42	W
Operating and storage temperature	$T_{\rm j},T_{\rm stg}$		-55 175	°C
Mounting torque		M3 and M3.5 screws	60	Mcm
Soldering temperature, wavesoldering only allowed at leads	$T_{\rm sold}$	1.6mm (0.063 in.) from case for 10s	260	°C



Parameter	Symbol	Conditions		Values		Unit
			min.	typ.	max.	
Thermal characteristics			·			
Thermal resistance, junction - case	R_{thJC}		-	-	3.6	K/W
Thermal resistance, junction - ambient	R_{thJA}	leaded	-	-	62	

Electrical characteristics, at T_i =25 °C, unless otherwise specified

Static characteristics

DC blocking voltage	V _{DC}	I _R =0.05 mA	600	-	-	V
Diode forward voltage	V_{F}	I _F =4 A, T _j =25 °C	ı	1.7	1.9	
		I _F =4 A, T _j =150 °C	ı	2	2.4	
Reverse current	I _R	V _R =600 V, T _j =25 °C	ı	0.5	50	μA
		V _R =600 V, T _j =150 °C		2	500	

Infineon Technologies components may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with

reasonably be expected to cause the f $Q_{\rm c}$	V _R =400 V,I _F ≤I _{F,max} ,	-	8	-	nC
aerospace device or system or to affect the saf $di_F/dt=200 \text{ A/µs}$,					
Life support systems are intended to b $t_{\it c}$	T _j =150 °C	-	-	<10	ns
and sustain and/or protect human life. C	$V_R=1 \text{ V}, f=\text{MHz}$	-	130	-	pF
of the user or other persons may be endangered.	V _R =600 V, f=1 MHz	-	20	-	

¹⁾ J-STD20 and JESD22

²⁾ All devices tested under avalanche conditions, for a time periode of 5ms, at 5mA.

 $^{^{3)}}$ t_c is the time constant for the capacitive displacement current waveform (independent from T_j , I_{LOAD} and di/dt), different from t_{rr} , which is dependent on T_j , I_{LOAD} , di/dt. No reverse recovery time constant t_{rr} due to absence of minority carrier injection.

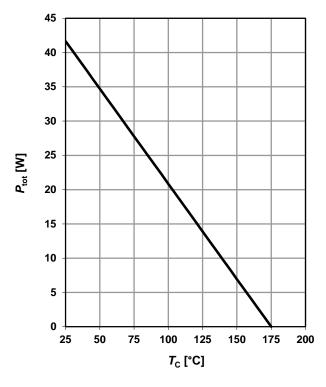
⁴⁾ Only capacitive charge occuring, guaranteed by design.



1 Power dissipation

 $P_{\text{tot}} = f(T_{\text{C}})$

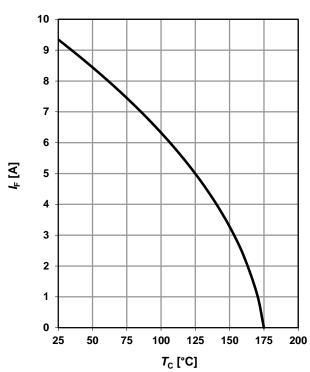
parameter: $R_{thJC(max)}$



2 Diode forward current

I_F=f(T_C); T_i≤175 °C

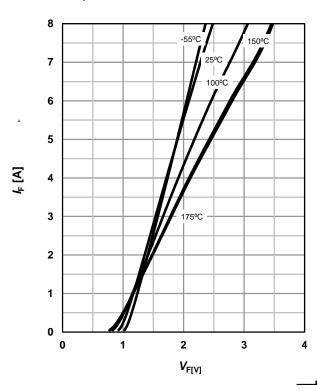
parameter: $R_{thJC(max)}$; $V_{F(max)}$



3 Typ. forward characteristic

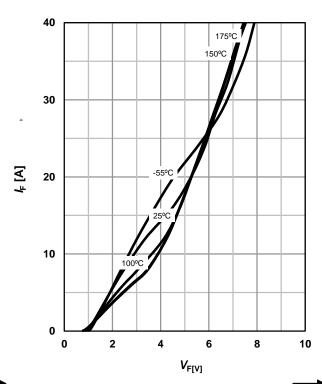
 $I_F=f(V_F)$; $t_p=400 \mu s$

parameter: T_i



4 Typ. forward characteristic in surge current mode

 $I_F = f(V_F)$; $t_p = 400 \mu s$; parameter: T_i

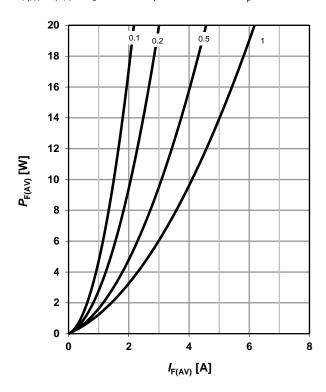




5 Typ. forward power dissipation vs.

average forward current

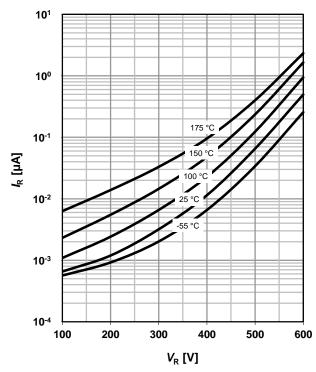
 $P_{F,AV}$ =f(I_F), T_C =100 °C, parameter: $D=t_p/T$



6 Typ. reverse current vs. reverse voltage

 $I_R=f(V_R)$

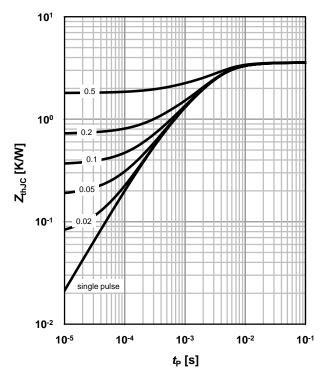
parameter: T_j



7 Transient thermal impedance

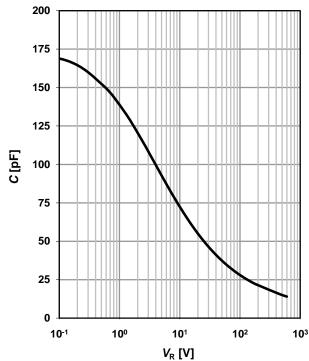
 $Z_{\mathrm{thJC}} = \mathrm{f}(t_{\mathrm{p}})$

parameter: $D=t_p/T$



8 Typ. capacitance vs. reverse voltage

C=f(V_R); T_C =25 °C, f=1 MHz



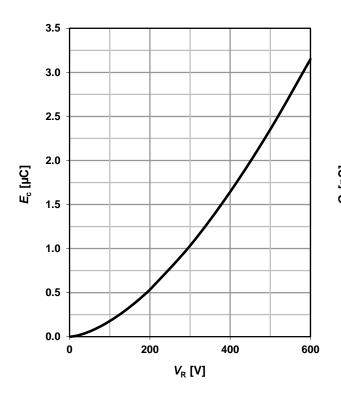


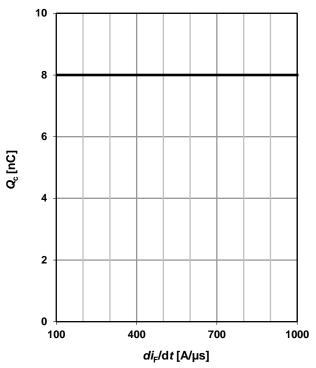
9 Typ. C stored energy

$E_{C}=f(V_{R})$

10 Typ. capacitance charge vs. current slope

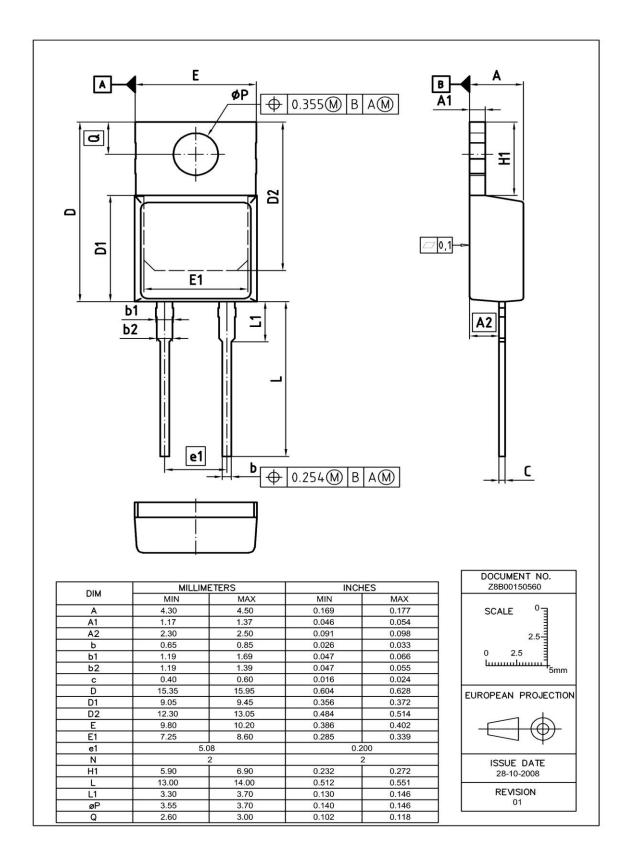
$$Q_{C}=f(di_{F}/dt)^{4}; T_{j}=150 \text{ °C}; I_{F} \leq I_{F,max}$$







PG-TO220-2: Outline





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